

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. LAM1P152D1/P0692D	Application No.: Filed Herewith
	Applicant: HO et al.	
	Filing Date Herewith	Group Unassigned

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
LV	A	5,230,772	07/27/93	Kadomura	156	643	07/25/91
	B	5,266,157	11/30/93	Kadomura	156	659.1	10/03/91
	C	5,741,396	04/21/98	Loewenstein	156	643.1	04/29/94
	D	5,814,563	09/29/98	Ding et al.	438	714	06/12/96
	E	5,877,032	03/02/99	Guinn et al.	438	9	08/27/96
	F	5,970,376	10/19/99	Chen	438	637	12/29/97
	G	6,037,255	03/14/00	Hussein et al.	438	675	05/12/99
	H	6,040,248	03/21/00	Chen et al.	438	725	06/24/98
LV	I	6,080,529	06/27/00	Ye et al.	430	318	10/19/98

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
LV	J	01/04707A1	01/18/01	WIPO	H01L	21/311	Yes	
	K	01/29879A2	04/26/01	WIPO	H01L	N/A	Yes	
	L	01/59825A1	08/16/01	WIPO	H01L	21/311	Yes	
	M	0851474A2	07/01/98	EPO	H01L	21/321	Yes	
LV	N	09036089	02/07/97	Japan	H01L	21/3065	Abs.	

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LV	O	Delsol et al., "Transformer Coupled Plasma Dielectric Etch for 0.25 μ m Technologies", Microelectronic Engineering 50 (2000), pages 75-80
LV	P	Eto et al., "High Selectivity Photoresist Ashing by the Addition of NH ₃ to CF ₄ /O ₂ or CHF ₃ /O ₂ ", SID 1999 Digest, pages 844-847
LV	Q	Hasegawa et al., "Copper Dual Damascene Interconnects with Low-K ($K_{eff} < 3.0$) Dielectrics Using FLARE TM and an Organo-Silicate Hard Mask", 1999 IEEE, pages 26.4.1. - 26.4.4.
Examiner LAN VINH		Date Considered 7/11/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
LV	AA	6,105,588	08/22/00	Li et al.	134	1.1	05/27/98
	BB	6,124,213	09/26/00	Usami et al.	438	710	11/17/98
	CC	6,153,511	11/28/00	Watatani	438	623	06/25/99
	DD	6,174,796B1	01/16/01	Takagi et al.	438	622	12/30/98
	EE	6,194,128B1	02/27/01	Tao et al.	430	313	09/17/98
	FF	6,245,663B1	06/12/01	Zhao et al.	438	622	09/30/98
	GG	6,352,918B1	03/05/02	Huang et al.	438	623	11/24/98
	HH	6,352,937B1	03/05/02	Kadomura et al.	438	725	04/27/98
LV	II	6,355,572B1	03/12/02	Ikegami	438	706	03/06/00

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	JJ							
	KK							
	LL							
	MM							
	NN							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LV	OO	Lin et al., "Microwave Imaging of Cerebral Edema", Proceedings of the IEEE, Vol. 70, No. 5, May 1982, pages 523-524
LV	PP	Plummer et al., "Silicon VLSI Technology - Fundamentals, Practice and Modeling", Department of Electrical Engineering, Stanford University (2000), page 639
LV	QQ	International Search Report, dated November 20, 2002
Examiner <i>LAV V/NM</i>		Date Considered <i>7/11/05</i>

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U.S. Patent Documents

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LV	AAA	6,620,733B2	09/16/03	Ho	438	700	02/12/01
	BBB						
	CCC						
	DDD						
	EEE						
	FFF						
	GGG						
	HHH						
	III						

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	JJJ							
	KKK							
	LLL							
	MMM							
	NNN							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LV	OOO	International Search Report, dated December 12, 2002
LV	PPP	International Search Report, dated July 22, 2003
	QQQ	
Examiner LAN VINH		Date Considered 7/11/05

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